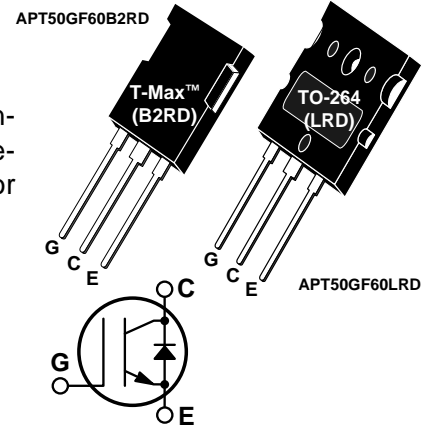


Fast IGBT & FRED

The Fast IGBT™ is a new generation of high voltage power IGBTs. Using Non-Punch Through™ Technology the Fast IGBT™ combined with an APT free-wheeling ultraFast Recovery Epitaxial Diode (FRED) offers superior ruggedness and fast switching speed.

- Low Forward Voltage Drop
- Low Tail Current
- RBSOA and SCSOA Rated
- Ultrafast Soft Recovery Antiparallel Diode
- High Freq. Switching to 20KHz
- Ultra Low Leakage Current



MAXIMUM RATINGS (IGBT)

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT50GF60B2RD/LRD	UNIT
V_{CES}	Collector-Emitter Voltage	600	Volts
V_{CGR}	Collector-Gate Voltage ($R_{GE} = 20K\Omega$)	600	
V_{GE}	Gate-Emitter Voltage	± 20	
I_{C1}	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	80	Amps
I_{C2}	Continuous Collector Current @ $T_C = 90^\circ\text{C}$	50	
I_{CM1}	Pulsed Collector Current ^① @ $T_C = 25^\circ\text{C}$	160	
I_{CM2}	Pulsed Collector Current ^① @ $T_C = 90^\circ\text{C}$	100	
P_D	Total Power Dissipation	300	Watts
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
T_L	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

STATIC ELECTRICAL CHARACTERISTICS (IGBT)

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{CES}	Collector-Emitter Breakdown Voltage ($V_{GE} = 0V, I_C = 0.50\text{mA}$)	600			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ($V_{CE} = V_{GE}, I_C = 700\mu\text{A}, T_J = 25^\circ\text{C}$)	4.5	5.5	6.5	
$V_{CE(ON)}$	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = I_{C2}, T_J = 25^\circ\text{C}$)		2.1	2.7	
	Collector-Emitter On Voltage ($V_{GE} = 15V, I_C = I_{C2}, T_J = 125^\circ\text{C}$)		2.2	2.8	
I_{CES}	Collector Cut-off Current ($V_{CE} = V_{CES}, V_{GE} = 0V, T_J = 25^\circ\text{C}$) ^②			0.50	mA
	Collector Cut-off Current ($V_{CE} = V_{CES}, V_{GE} = 0V, T_J = 125^\circ\text{C}$) ^②			TBD	
I_{GES}	Gate-Emitter Leakage Current ($V_{GE} = \pm 20V, V_{CE} = 0V$)			± 100	nA

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

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DYNAMIC CHARACTERISTICS (IGBT)

APT50GF60B2RD/LRD

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C _{ies}	Input Capacitance	Capacitance V _{GE} = 0V V _{CE} = 25V f = 1 MHz		2600	3600	pF
C _{oes}	Output Capacitance			475	710	
C _{res}	Reverse Transfer Capacitance			165	250	
Q _g	Total Gate Charge ^③	Gate Charge V _{GE} = 15V V _{CC} = 0.5V _{CES} I _C = I _{C2}		170	225	nC
Q _{ge}	Gate-Emitter Charge			25	45	
Q _{gc}	Gate-Collector ("Miller") Charge			100	140	
t _{d(on)}	Turn-on Delay Time	Resistive Switching (25°C) V _{GE} = 15V V _{CC} = .8V _{CES} I _C = I _{C2} R _G = 10Ω		20		ns
t _r	Rise Time			100		
t _{d(off)}	Turn-off Delay Time			160		
t _f	Fall Time			200		
t _{d(on)}	Turn-on Delay Time	Inductive Switching (150°C) V _{CLAMP(Peak)} = 0.66V _{CES} V _{GE} = 15V I _C = I _{C2} R _G = 10Ω T _J = +150°C		30	50	ns
t _r	Rise Time			90	135	
t _{d(off)}	Turn-off Delay Time			290	435	
t _f	Fall Time			170	340	
E _{on}	Turn-on Switching Energy ^④			2.2		mJ
E _{off}	Turn-off Switching Energy			2.4		
E _{ts}	Total Switching Losses ^④			4.6		
t _{d(on)}	Turn-on Delay Time	Inductive Switching (25°C) V _{CLAMP(Peak)} = 0.66V _{CES} V _{GE} = 15V I _C = I _{C2} R _G = 10Ω T _J = +25°C		30		ns
t _r	Rise Time			90		
t _{d(off)}	Turn-off Delay Time			260		
t _f	Fall Time			100		
E _{ts}	Total Switching Losses ^④			4.3		mJ
g _{fe}	Forward Transconductance	V _{CE} = 20V, I _C = I _{C2}	6			S

THERMAL AND MECHANICAL CHARACTERISTICS (IGBT and FRED)

Symbol	Characteristic	MIN	TYP	MAX	UNIT
R _{θJC}	Junction to Case (IGBT)			0.42	°C/W
	Junction to Case (FRED)			0.66	
R _{θJA}	Junction to Ambient			40	
W _T	Package Weight		0.22		oz
			6.1		gm
Torque	Mounting Torque using a 6-32 or 3mm Binding Head Machine Screw			10	lb•in
				1.1	N•m

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Leakages include the FRED and IGBT.

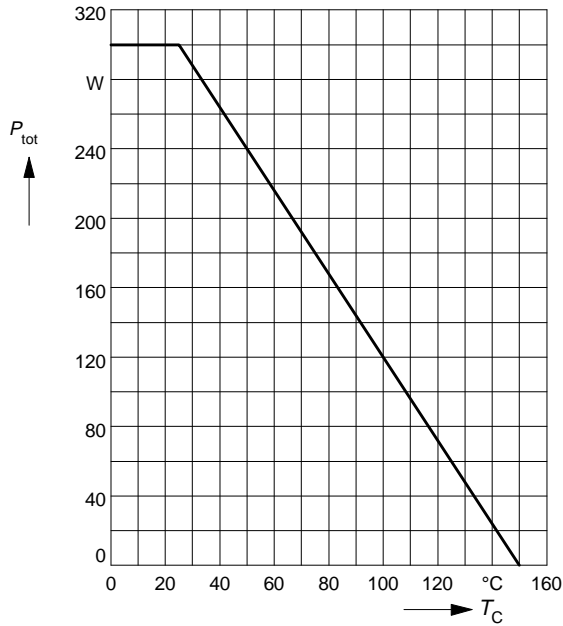
③ See MIL-STD-750 Method 3471

④ Switching losses include the FRED and IGBT.

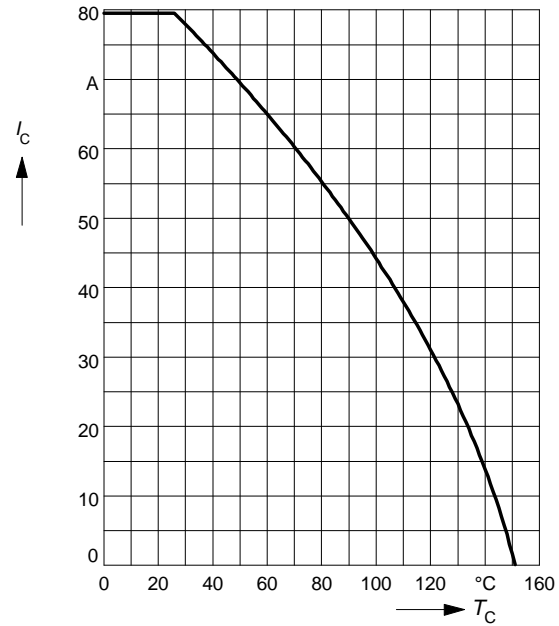
APT Reserves the right to change, without notice, the specifications and information contained herein.

Power dissipation

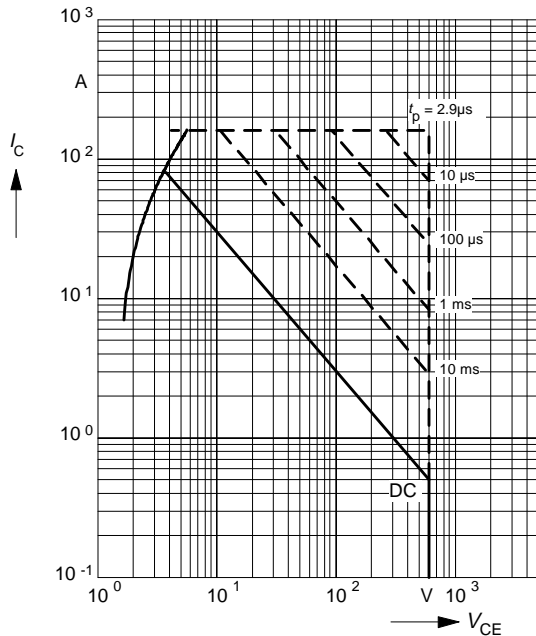
$$P_{\text{tot}} = f(T_C)$$

 parameter: $T_j \leq 150\text{ }^\circ\text{C}$

Collector current

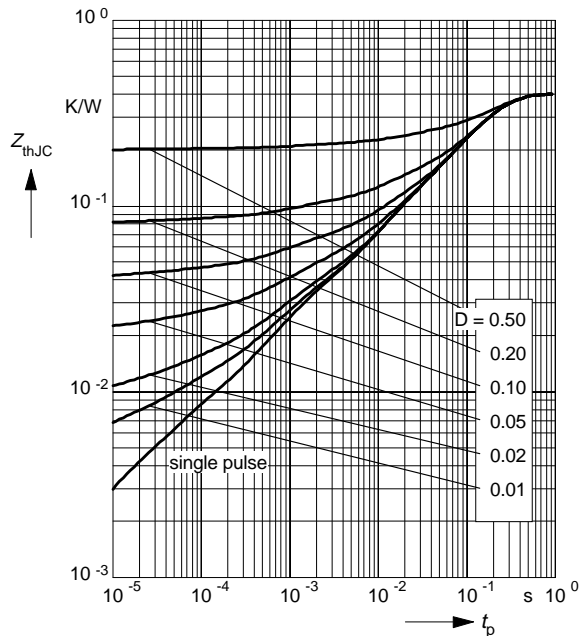
$$I_C = f(T_C)$$

 parameter: $V_{GE} \geq 15\text{ V}$, $T_j \leq 150\text{ }^\circ\text{C}$

Safe operating area

$$I_C = f(V_{CE})$$

 parameter: $D = 0$, $T_C = 25\text{ }^\circ\text{C}$, $T_j \leq 150\text{ }^\circ\text{C}$

Transient thermal impedance IGBT

$$Z_{\text{thJC}} = f(t_p)$$

 parameter: $D = t_p / T$

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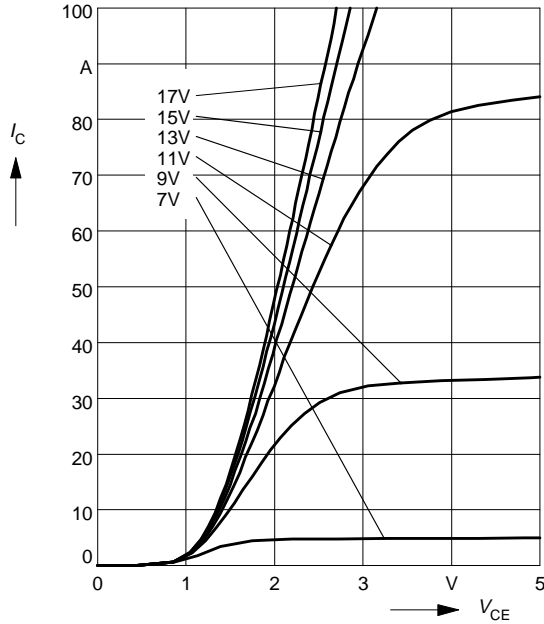
F-33700 Merignac - France

Bend, Oregon 97702-1035

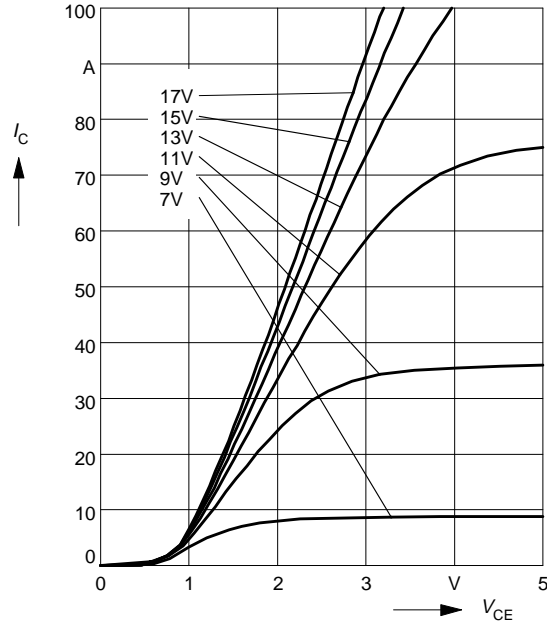
Phone: (33) 5 57 92 15 15
Phone: (541) 382-8028
FAX: (33) 5 56 47 97 61
FAX: (541) 388-0364

Typ. output characteristics

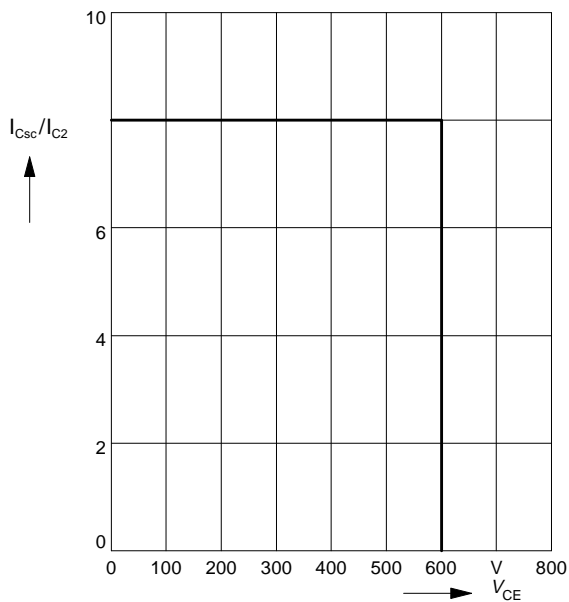
$$I_C = f(V_{CE})$$

 parameter: $t_p = 80 \mu s$, $T_j = 25^\circ C$

Typ. output characteristics

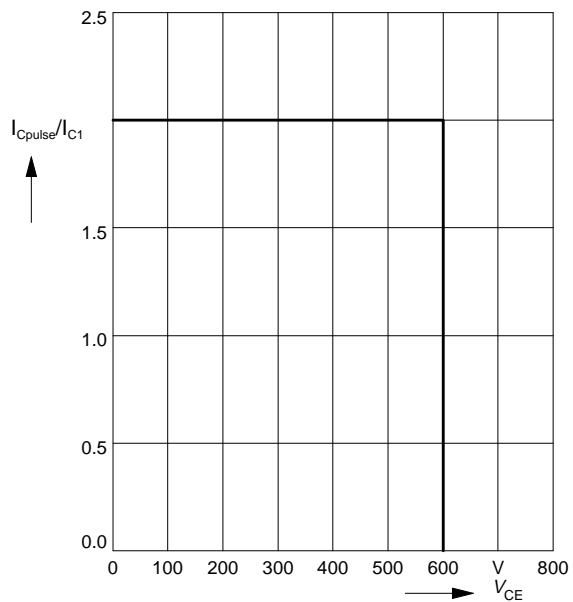
$$I_C = f(V_{CE})$$

 parameter: $t_p = 80 \mu s$, $T_j = 125^\circ C$

Short circuit safe operating area

$$I_{Csc} = f(V_{CE}), T_j = 150^\circ C$$

 parameter: $V_{GE} = \pm 15 V$, $t_{sc} \leq 10 \mu s$, $L < 50 nH$

Reverse biased safe operating area

$$I_{Cpuls} = f(V_{CE}), T_j = 150^\circ C$$

 parameter: $V_{GE} = 15 V$


ULTRAFAST SOFT RECOVERY PARALLEL DIODE

MAXIMUM RATINGS (FRED)

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT50GF60B2RD/LRD	UNIT
V_R	Maximum D.C. Reverse Voltage	600	Volts
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		
V_{RWM}	Maximum Working Peak Reverse Voltage		
$I_F(AV)$	Maximum Average Forward Current ($T_C = 85^\circ\text{C}$, Duty Cycle = 0.5)	60	Amps
$I_F(RMS)$	RMS Forward Current	100	
I_{FSM}	Non-Repetitive Forward Surge Current ($T_J = 45^\circ\text{C}$, 8.3ms)	600	

STATIC ELECTRICAL CHARACTERISTICS (FRED)

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
V_F	Maximum Forward Voltage			1.8	Volts
				$I_F = 60\text{A}$	
			$I_F = 120\text{A}$	1.75	
	$I_F = 60\text{A}, T_J = 150^\circ\text{C}$			1.5	

DYNAMIC CHARACTERISTICS (FRED)

Symbol	Characteristic	MIN	TYP	MAX	UNIT
t_{rr1}	Reverse Recovery Time, $I_F = 1.0\text{A}$, $di_F/dt = -15\text{A}/\mu\text{s}$, $V_R = 30\text{V}$, $T_J = 25^\circ\text{C}$		55	70	ns
t_{rr2}	Reverse Recovery Time		$T_J = 25^\circ\text{C}$ 70		
t_{rr3}	$I_F = 60\text{A}$, $di_F/dt = -480\text{A}/\mu\text{s}$, $V_R = 350\text{V}$		$T_J = 100^\circ\text{C}$ 90		
t_{fr1}	Forward Recovery Time		$T_J = 25^\circ\text{C}$ 160		Volts
t_{fr2}	$I_F = 60\text{A}$, $di_F/dt = 480\text{A}/\mu\text{s}$, $V_R = 350\text{V}$		$T_J = 100^\circ\text{C}$ 160		
I_{RRM1}	Reverse Recovery Current		$T_J = 25^\circ\text{C}$ 10	17	Amps
I_{RRM2}	$I_F = 60\text{A}$, $di_F/dt = -480\text{A}/\mu\text{s}$, $V_R = 350\text{V}$		$T_J = 100^\circ\text{C}$ 20	30	
Q_{rr1}	Recovery Charge		$T_J = 25^\circ\text{C}$ 350		nC
Q_{rr2}	$I_F = 60\text{A}$, $di_F/dt = -480\text{A}/\mu\text{s}$, $V_R = 350\text{V}$		$T_J = 100^\circ\text{C}$ 900		
V_{fr1}	Forward Recovery Voltage		$T_J = 25^\circ\text{C}$ 6		Volts
V_{fr2}	$I_F = 60\text{A}$, $di_F/dt = 480\text{A}/\mu\text{s}$, $V_R = 350\text{V}$		$T_J = 100^\circ\text{C}$ 6		
diM/dt	Rate of Fall of Recovery Current		$T_J = 25^\circ\text{C}$ 800		A/ μs
	$I_F = 60\text{A}$, $di_F/dt = -480\text{A}/\mu\text{s}$, $V_R = 350\text{V}$		$T_J = 100^\circ\text{C}$ 500		

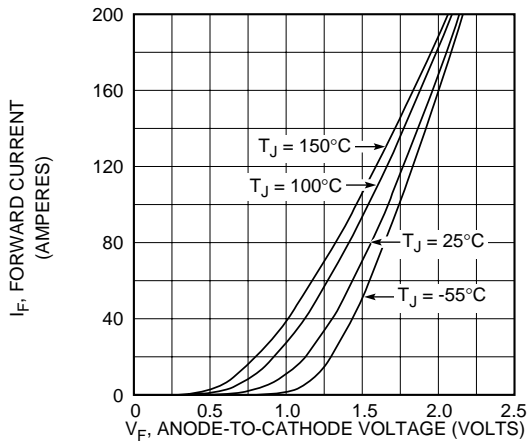


Figure 1, Forward Voltage Drop vs Forward Current

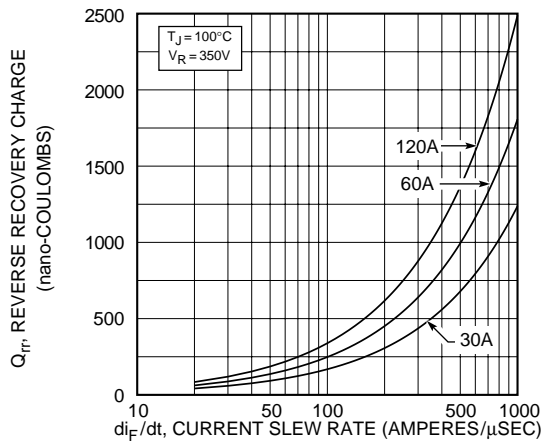


Figure 2, Reverse Recovery Charge vs Current Slew Rate

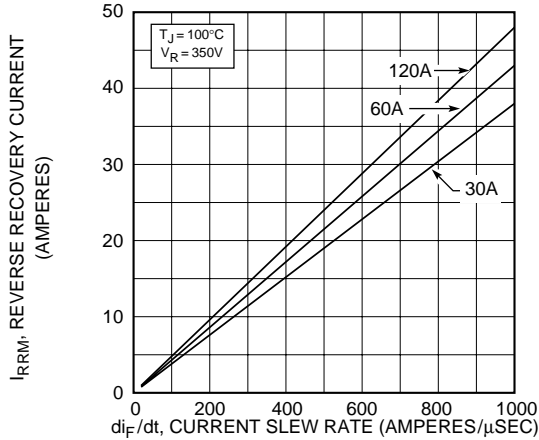


Figure 3, Reverse Recovery Current vs Current Slew Rate

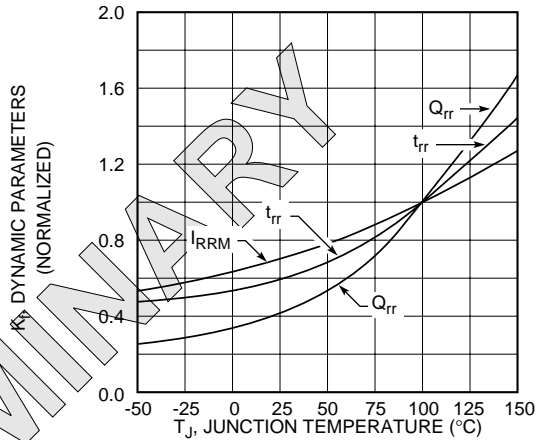


Figure 4, Dynamic Parameters vs Junction Temperature

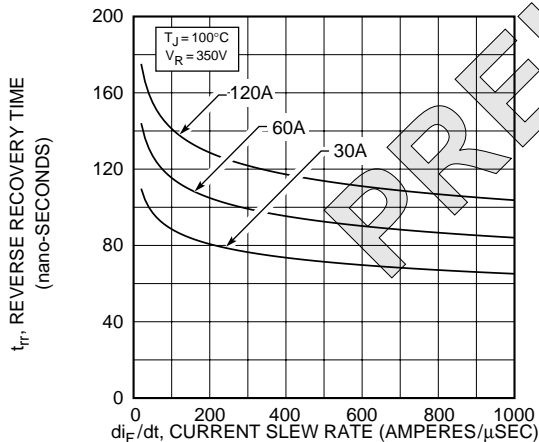


Figure 5, Reverse Recovery Time vs Current Slew Rate

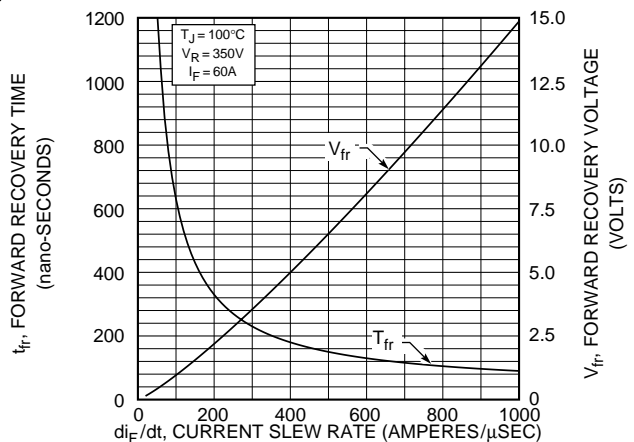


Figure 6, Forward Recovery Voltage/Time vs Current Slew Rate

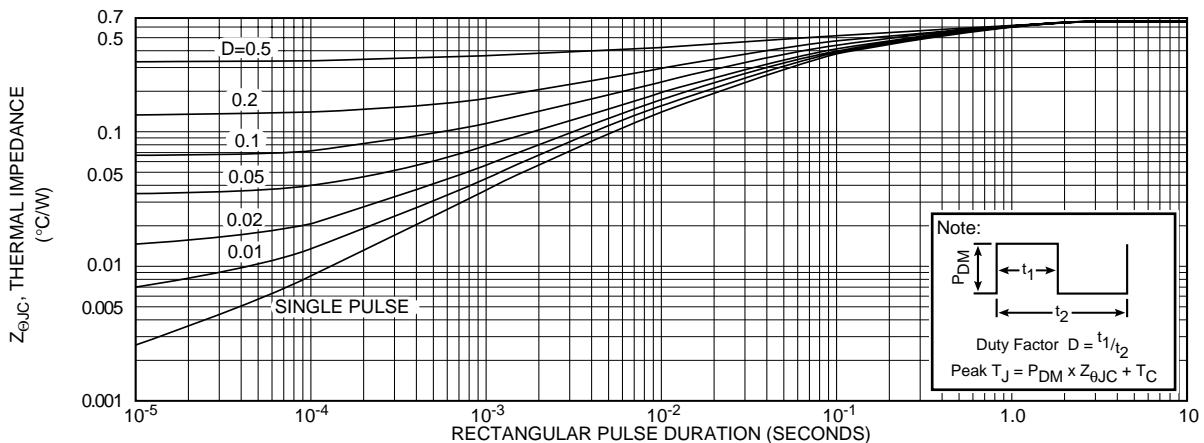


Figure 7, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

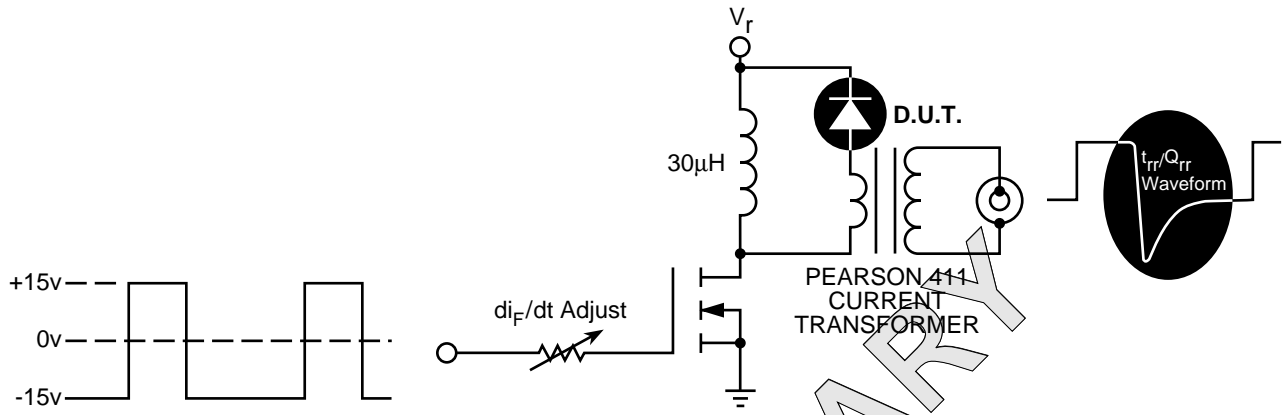


Figure 25, Diode Reverse Recovery Test Circuit and Waveforms

1 I_F - Forward Conduction Current

2 di_F/dt - Current Slew Rate, Rate of Forward Current Change Through Zero Crossing

3 I_{RRM} - Peak Reverse Recovery Current.

4 t_{rr} - Reverse Recovery Time Measured from Point of I_F Current Falling Through Zero to a Tangent Line { 6 diM/dt } Extrapolated Through Zero Defined by 0.75 and 0.50 I_{RRM} .

5 Q_{rr} - Area Under the Curve Defined by I_{RRM} and t_{rr} .

6 diM/dt - Maximum Rate of Current Change During the Trailing Portion of t_{rr} .

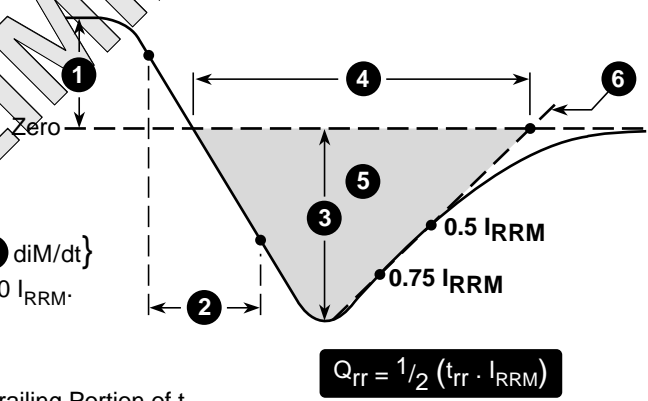


Figure 8, Diode Reverse Recovery Waveform and Definitions

